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Understanding [Embedded - CPLDs \(Complex Programmable Logic Devices\)](#)

Embedded - CPLDs, or Complex Programmable Logic Devices, are highly versatile digital logic devices used in electronic systems. These programmable components are designed to perform complex logical operations and can be customized for specific applications. Unlike fixed-function ICs, CPLDs offer the flexibility to reprogram their configuration, making them an ideal choice for various embedded systems. They consist of a set of logic gates and programmable interconnects, allowing designers to implement complex logic circuits without needing custom hardware.

Applications of Embedded - CPLDs

Details

Product Status	Active
Programmable Type	In System Programmable
Delay Time tpd(1) Max	5.4 ns
Voltage Supply - Internal	1.71V ~ 1.89V
Number of Logic Elements/Blocks	570
Number of Macrocells	440
Number of Gates	-
Number of I/O	76
Operating Temperature	0°C ~ 85°C (TJ)
Mounting Type	Surface Mount
Package / Case	100-LBGA
Supplier Device Package	100-FBGA (11x11)
Purchase URL	https://www.e-xfl.com/product-detail/intel/epm570gf100c5n

Introduction

The MAX[®] II family of instant-on, non-volatile CPLDs is based on a 0.18- μ m, 6-layer-metal-flash process, with densities from 240 to 2,210 logic elements (LEs) (128 to 2,210 equivalent macrocells) and non-volatile storage of 8 Kbits. MAX II devices offer high I/O counts, fast performance, and reliable fitting versus other CPLD architectures. Featuring MultiVolt core, a user flash memory (UFM) block, and enhanced in-system programmability (ISP), MAX II devices are designed to reduce cost and power while providing programmable solutions for applications such as bus bridging, I/O expansion, power-on reset (POR) and sequencing control, and device configuration control.

Features

The MAX II CPLD has the following features:

- Low-cost, low-power CPLD
- Instant-on, non-volatile architecture
- Standby current as low as 25 μ A
- Provides fast propagation delay and clock-to-output times
- Provides four global clocks with two clocks available per logic array block (LAB)
- UFM block up to 8 Kbits for non-volatile storage
- MultiVolt core enabling external supply voltages to the device of either 3.3 V/2.5 V or 1.8 V
- MultiVolt I/O interface supporting 3.3-V, 2.5-V, 1.8-V, and 1.5-V logic levels
- Bus-friendly architecture including programmable slew rate, drive strength, bus-hold, and programmable pull-up resistors
- Schmitt triggers enabling noise tolerant inputs (programmable per pin)
- I/Os are fully compliant with the Peripheral Component Interconnect Special Interest Group (PCI SIG) PCI Local Bus Specification, Revision 2.2 for 3.3-V operation at 66 MHz
- Supports hot-socketing
- Built-in Joint Test Action Group (JTAG) boundary-scan test (BST) circuitry compliant with IEEE Std. 1149.1-1990
- ISP circuitry compliant with IEEE Std. 1532

Table 1-6. Document Revision History

Date and Revision	Changes Made	Summary of Changes
June 2005, version 1.3	■ Updated timing numbers in Table 1-1.	—
December 2004, version 1.2	■ Updated timing numbers in Table 1-1.	—
June 2004, version 1.1	■ Updated timing numbers in Table 1-1.	—

Introduction

This chapter describes the architecture of the MAX II device and contains the following sections:

- “Functional Description” on page 2–1
- “Logic Array Blocks” on page 2–4
- “Logic Elements” on page 2–6
- “MultiTrack Interconnect” on page 2–12
- “Global Signals” on page 2–16
- “User Flash Memory Block” on page 2–18
- “MultiVolt Core” on page 2–22
- “I/O Structure” on page 2–23

Functional Description

MAX® II devices contain a two-dimensional row- and column-based architecture to implement custom logic. Row and column interconnects provide signal interconnects between the logic array blocks (LABs).

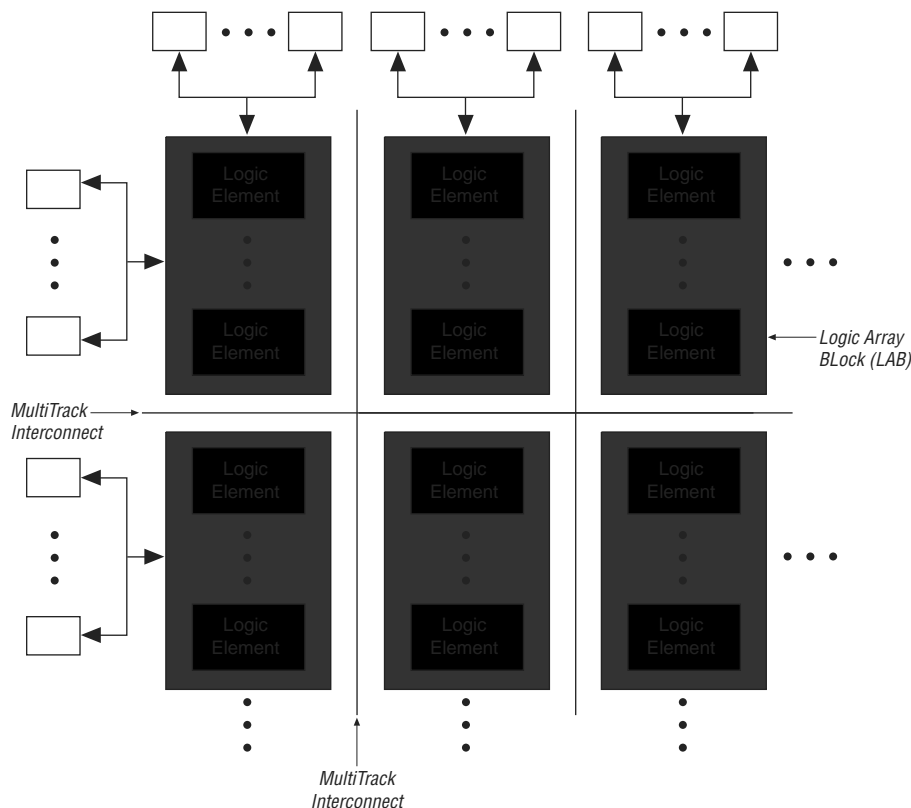
The logic array consists of LABs, with 10 logic elements (LEs) in each LAB. An LE is a small unit of logic providing efficient implementation of user logic functions. LABs are grouped into rows and columns across the device. The MultiTrack interconnect provides fast granular timing delays between LABs. The fast routing between LEs provides minimum timing delay for added levels of logic versus globally routed interconnect structures.

The MAX II device I/O pins are fed by I/O elements (IOE) located at the ends of LAB rows and columns around the periphery of the device. Each IOE contains a bidirectional I/O buffer with several advanced features. I/O pins support Schmitt trigger inputs and various single-ended standards, such as 66-MHz, 32-bit PCI, and LVTTTL.

MAX II devices provide a global clock network. The global clock network consists of four global clock lines that drive throughout the entire device, providing clocks for all resources within the device. The global clock lines can also be used for control signals such as clear, preset, or output enable.

Figure 2–1 shows a functional block diagram of the MAX II device.

Figure 2–1. MAX II Device Block Diagram



Each MAX II device contains a flash memory block within its floorplan. On the EPM240 device, this block is located on the left side of the device. On the EPM570, EPM1270, and EPM2210 devices, the flash memory block is located on the bottom-left area of the device. The majority of this flash memory storage is partitioned as the dedicated configuration flash memory (CFM) block. The CFM block provides the non-volatile storage for all of the SRAM configuration information. The CFM automatically downloads and configures the logic and I/O at power-up, providing instant-on operation.



For more information about configuration upon power-up, refer to the *Hot Socketing and Power-On Reset in MAX II Devices* chapter in the *MAX II Device Handbook*.

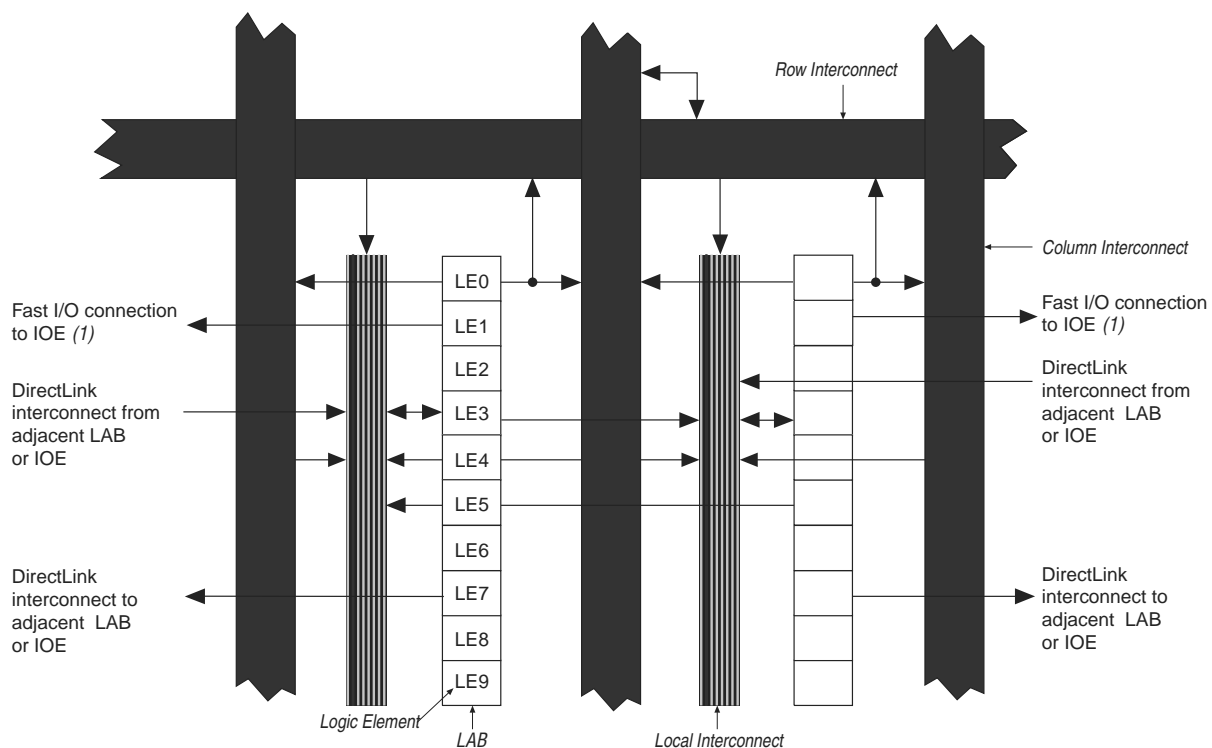
A portion of the flash memory within the MAX II device is partitioned into a small block for user data. This user flash memory (UFM) block provides 8,192 bits of general-purpose user storage. The UFM provides programmable port connections to the logic array for reading and writing. There are three LAB rows adjacent to this block, with column numbers varying by device.

Table 2–1 shows the number of LAB rows and columns in each device, as well as the number of LAB rows and columns adjacent to the flash memory area in the EPM570, EPM1270, and EPM2210 devices. The long LAB rows are full LAB rows that extend from one side of row I/O blocks to the other. The short LAB rows are adjacent to the UFM block; their length is shown as width in LAB columns.

Logic Array Blocks

Each LAB consists of 10 LEs, LE carry chains, LAB control signals, a local interconnect, a look-up table (LUT) chain, and register chain connection lines. There are 26 possible unique inputs into an LAB, with an additional 10 local feedback input lines fed by LE outputs in the same LAB. The local interconnect transfers signals between LEs in the same LAB. LUT chain connections transfer the output of one LE's LUT to the adjacent LE for fast sequential LUT connections within the same LAB. Register chain connections transfer the output of one LE's register to the adjacent LE's register within an LAB. The Quartus® II software places associated logic within an LAB or adjacent LABs, allowing the use of local, LUT chain, and register chain connections for performance and area efficiency. Figure 2-3 shows the MAX II LAB.

Figure 2-3. MAX II LAB Structure



Note to Figure 2-3:

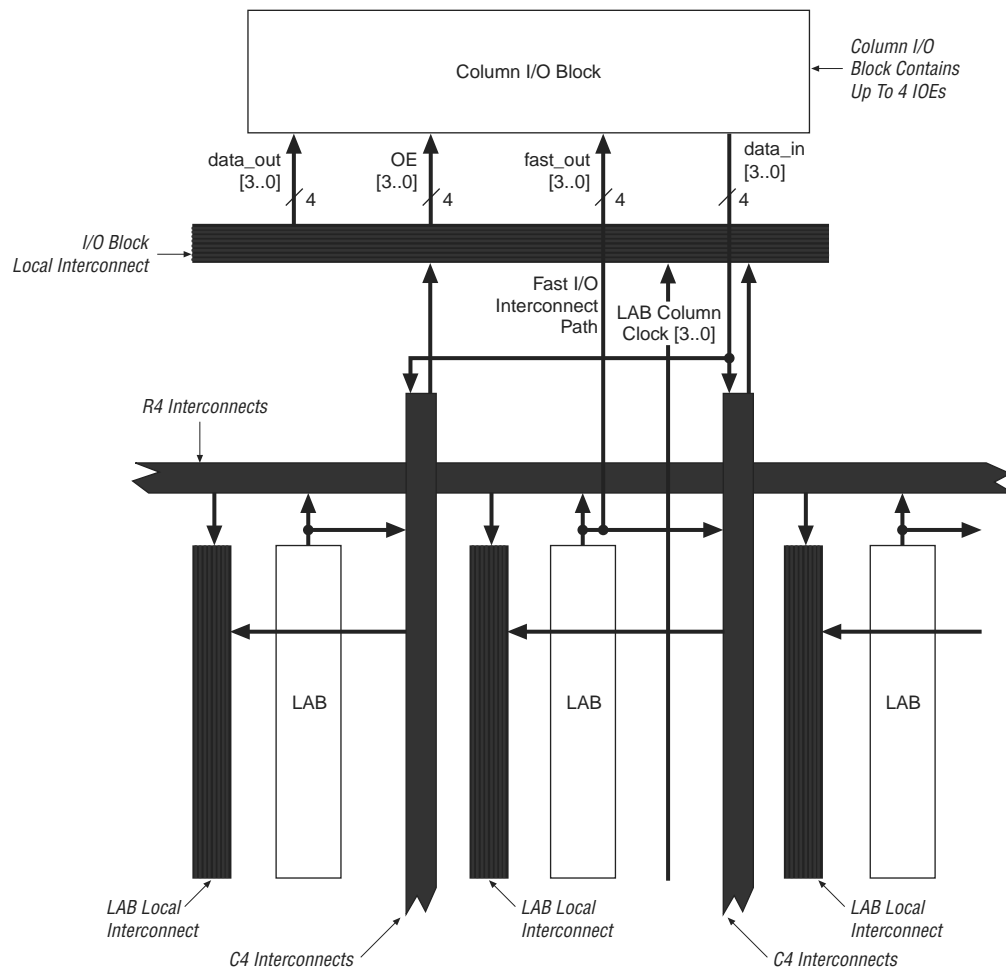
(1) Only from LABs adjacent to IOEs.

LAB Interconnects

The LAB local interconnect can drive LEs within the same LAB. The LAB local interconnect is driven by column and row interconnects and LE outputs within the same LAB. Neighboring LABs, from the left and right, can also drive an LAB's local interconnect through the DirectLink connection. The DirectLink connection feature minimizes the use of row and column interconnects, providing higher performance and flexibility. Each LE can drive 30 other LEs through fast local and DirectLink interconnects. Figure 2-4 shows the DirectLink connection.

Figure 2–21 shows how a column I/O block connects to the logic array.

Figure 2–21. Column I/O Block Connection to the Interconnect (*Note 1*)



Note to Figure 2–21:

(1) Each of the four IOEs in the column I/O block can have one `data_out` or `fast_out` output, one `OE` output, and one `data_in` input.

I/O Standards and Banks

MAX II device IOEs support the following I/O standards:

- 3.3-V LVTTTL/LVCMOS
- 2.5-V LVTTTL/LVCMOS
- 1.8-V LVTTTL/LVCMOS
- 1.5-V LVCMOS
- 3.3-V PCI

Table 2-6. Programmable Drive Strength (*Note 1*)

I/O Standard	IOH/IOL Current Strength Setting (mA)
3.3-V LVTTTL	16
	8
3.3-V LVCMOS	8
	4
2.5-V LVTTTL/LVCMOS	14
	7
1.8-V LVTTTL/LVCMOS	6
	3
1.5-V LVCMOS	4
	2

Note to Table 2-6:

- (1) The I_{OH} current strength numbers shown are for a condition of a $V_{OUT} = V_{OH}$ minimum, where the V_{OH} minimum is specified by the I/O standard. The I_{OL} current strength numbers shown are for a condition of a $V_{OUT} = V_{OL}$ maximum, where the V_{OL} maximum is specified by the I/O standard. For 2.5-V LVTTTL/LVCMOS, the I_{OH} condition is $V_{OUT} = 1.7$ V and the I_{OL} condition is $V_{OUT} = 0.7$ V.

Slew-Rate Control

The output buffer for each MAX II device I/O pin has a programmable output slew-rate control that can be configured for low noise or high-speed performance. A faster slew rate provides high-speed transitions for high-performance systems. However, these fast transitions may introduce noise transients into the system. A slow slew rate reduces system noise, but adds a nominal output delay to rising and falling edges. The lower the voltage standard (for example, 1.8-V LVTTTL) the larger the output delay when slow slew is enabled. Each I/O pin has an individual slew-rate control, allowing the designer to specify the slew rate on a pin-by-pin basis. The slew-rate control affects both the rising and falling edges.

Open-Drain Output

MAX II devices provide an optional open-drain (equivalent to open-collector) output for each I/O pin. This open-drain output enables the device to provide system-level control signals (for example, interrupt and write enable signals) that can be asserted by any of several devices. This output can also provide an additional wired-OR plane.

Programmable Ground Pins

Each unused I/O pin on MAX II devices can be used as an additional ground pin. This programmable ground feature does not require the use of the associated LEs in the device. In the Quartus II software, unused pins can be set as programmable GND on a global default basis or they can be individually assigned. Unused pins also have the option of being set as tri-stated input pins.

Document Revision History

Table 2-8 shows the revision history for this chapter.

Table 2-8. Document Revision History

Date and Revision	Changes Made	Summary of Changes
October 2008, version 2.2	<ul style="list-style-type: none"> ■ Updated Table 2-4 and Table 2-6. ■ Updated “I/O Standards and Banks” section. ■ Updated New Document Format. 	—
March 2008, version 2.1	<ul style="list-style-type: none"> ■ Updated “Schmitt Trigger” section. 	—
December 2007, version 2.0	<ul style="list-style-type: none"> ■ Updated “Clear and Preset Logic Control” section. ■ Updated “MultiVolt Core” section. ■ Updated “MultiVolt I/O Interface” section. ■ Updated Table 2-7. ■ Added “Referenced Documents” section. 	Updated document with MAX IIZ information.
December 2006, version 1.7	<ul style="list-style-type: none"> ■ Minor update in “Internal Oscillator” section. Added document revision history. 	—
August 2006, version 1.6	<ul style="list-style-type: none"> ■ Updated functional description and I/O structure sections. 	—
July 2006, version 1.5	<ul style="list-style-type: none"> ■ Minor content and table updates. 	—
February 2006, version 1.4	<ul style="list-style-type: none"> ■ Updated “LAB Control Signals” section. ■ Updated “Clear and Preset Logic Control” section. ■ Updated “Internal Oscillator” section. ■ Updated Table 2-5. 	—
August 2005, version 1.3	<ul style="list-style-type: none"> ■ Removed Note 2 from Table 2-7. 	—
December 2004, version 1.2	<ul style="list-style-type: none"> ■ Added a paragraph to page 2-15. 	—
June 2004, version 1.1	<ul style="list-style-type: none"> ■ Added CFM acronym. Corrected Figure 2-19. 	—

Table 3-3. 32-Bit MAX II Device IDCODE (Part 2 of 2)

Device	Binary IDCODE (32 Bits) (1)				HEX IDCODE
	Version (4 Bits)	Part Number	Manufacturer Identity (11 Bits)	LSB (1 Bit) (2)	
EPM240Z	0000	0010 0000 1010 0101	000 0110 1110	1	0x020A50DD
EPM570Z	0000	0010 0000 1010 0110	000 0110 1110	1	0x020A60DD

Notes to Table 3-2:

- (1) The most significant bit (MSB) is on the left.
- (2) The IDCODE's least significant bit (LSB) is always 1.



For JTAG AC characteristics, refer to the *DC and Switching Characteristics* chapter in the *MAX II Device Handbook*.



For more information about JTAG BST, refer to the *IEEE 1149.1 (JTAG) Boundary-Scan Testing for MAX II Devices* chapter in the *MAX II Device Handbook*.

JTAG Block

The MAX II JTAG block feature allows you to access the JTAG TAP and state signals when either the USER0 or USER1 instruction is issued to the JTAG TAP. The USER0 and USER1 instructions bring the JTAG boundary-scan chain (TDI) through the user logic instead of the MAX II device's boundary-scan cells. Each USER instruction allows for one unique user-defined JTAG chain into the logic array.

Parallel Flash Loader

The JTAG block ability to interface JTAG to non-JTAG devices is ideal for general-purpose flash memory devices (such as Intel- or Fujitsu-based devices) that require programming during in-circuit test. The flash memory devices can be used for FPGA configuration or be part of system memory. In many cases, the MAX II device is already connected to these devices as the configuration control logic between the FPGA and the flash device. Unlike ISP-capable CPLD devices, bulk flash devices do not have JTAG TAP pins or connections. For small flash devices, it is common to use the serial JTAG scan chain of a connected device to program the non-JTAG flash device. This is slow and inefficient in most cases and impractical for large parallel flash devices. Using the MAX II device's JTAG block as a parallel flash loader, with the Quartus II software, to program and verify flash contents provides a fast and cost-effective means of in-circuit programming during test. Figure 3-1 shows MAX II being used as a parallel flash loader.

Real-Time ISP

For systems that require more than DC logic level control of I/O pins, the real-time ISP feature allows you to update the CFM block with a new design image while the current design continues to operate in the SRAM logic array and I/O pins. A new programming file is updated into the MAX II device without halting the original design's operation, saving down-time costs for remote or field upgrades. The updated CFM block configures the new design into the SRAM upon the next power cycle. It is also possible to execute an immediate configuration of the SRAM without a power cycle by using a specific sequence of ISP commands. The configuration of SRAM without a power cycle takes a specific amount of time (t_{CONFIG}). During this time, the I/O pins are tri-stated and weakly pulled-up to V_{CCIO} .

Design Security

All MAX II devices contain a programmable security bit that controls access to the data programmed into the CFM block. When this bit is programmed, design programming information, stored in the CFM block, cannot be copied or retrieved. This feature provides a high level of design security because programmed data within flash memory cells is invisible. The security bit that controls this function, as well as all other programmed data, is reset only when the device is erased. The SRAM is also invisible and cannot be accessed regardless of the security bit setting. The UFM block data is not protected by the security bit and is accessible through JTAG or logic array connections.

Programming with External Hardware


MAX II devices can be programmed by downloading the information via in-circuit testers, embedded processors, the Altera® ByteblasterMV™, MasterBlaster™, ByteBlaster™ II, and USB-Blaster cables.

BP Microsystems, System General, and other programming hardware manufacturers provide programming support for Altera devices. Check their websites for device support information.

Referenced Documents

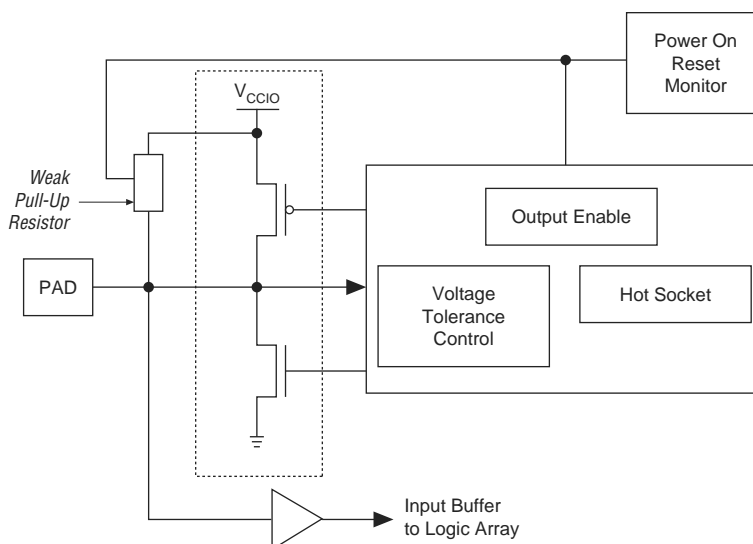
This chapter references the following documents:

- *DC and Switching Characteristics* chapter in the *MAX II Device Handbook*
- *IEEE 1149.1 (JTAG) Boundary-Scan Testing for MAX II Devices* chapter in the *MAX II Device Handbook*
- *Real-Time ISP and ISP Clamp for MAX II Devices* chapter in the *MAX II Device Handbook*
- *Using Jam STAPL for ISP via an Embedded Processor* chapter in the *MAX II Device Handbook*

 Make sure that the V_{CCINT} is within the recommended operating range even though SRAM download has completed.

Each I/O and clock pin has the circuitry shown in Figure 4-1.

Figure 4-1. Hot Socketing Circuit Block Diagram for MAX II Devices



The POR circuit monitors V_{CCINT} and V_{CCIO} voltage levels and keeps I/O pins tri-stated until the device has completed its flash memory configuration of the SRAM logic. The weak pull-up resistor (R) from the I/O pin to V_{CCIO} is enabled during download to keep the I/O pins from floating. The 3.3-V tolerance control circuit permits the I/O pins to be driven by 3.3 V before V_{CCIO} and/or V_{CCINT} are powered, and it prevents the I/O pins from driving out when the device is not fully powered or operational. The hot socket circuit prevents I/O pins from internally powering V_{CCIO} and V_{CCINT} when driven by external signals before the device is powered.


 For information about 5.0-V tolerance, refer to the *Using MAX II Devices in Multi-Voltage Systems* chapter in the *MAX II Device Handbook*.

Figure 4-2 shows a transistor-level cross section of the MAX II device I/O buffers. This design ensures that the output buffers do not drive when V_{CCIO} is powered before V_{CCINT} or if the I/O pad voltage is higher than V_{CCIO} . This also applies for sudden voltage spikes during hot insertion. The V_{PAD} leakage current charges the 3.3-V tolerant circuit capacitance.

Power-Up Characteristics

When power is applied to a MAX II device, the POR circuit monitors V_{CCINT} and begins SRAM download at an approximate voltage of 1.7 V or 1.55 V for MAX IIG and MAX IIZ devices. From this voltage reference, SRAM download and entry into user mode takes 200 to 450 μ s maximum, depending on device density. This period of time is specified as t_{CONFIG} in the power-up timing section of the *DC and Switching Characteristics* chapter in the *MAX II Device Handbook*.

Entry into user mode is gated by whether all V_{CCIO} banks are powered with sufficient operating voltage. If V_{CCINT} and V_{CCIO} are powered simultaneously, the device enters user mode within the t_{CONFIG} specifications. If V_{CCIO} is powered more than t_{CONFIG} after V_{CCINT} , the device does not enter user mode until 2 μ s after all V_{CCIO} banks are powered.

For MAX II and MAX IIG devices, when in user mode, the POR circuitry continues to monitor the V_{CCINT} (but not V_{CCIO}) voltage level to detect a brown-out condition. If there is a V_{CCINT} voltage sag at or below 1.4 V during user mode, the POR circuit resets the SRAM and tri-states the I/O pins. Once V_{CCINT} rises back to approximately 1.7 V (or 1.55 V for MAX IIG devices), the SRAM download restarts and the device begins to operate after t_{CONFIG} time has passed.

For MAX IIZ devices, the POR circuitry does not monitor the V_{CCINT} and V_{CCIO} voltage levels after the device enters user mode. If there is a V_{CCINT} voltage sag below 1.4 V during user mode, the functionality of the device will not be guaranteed and you must power down the V_{CCINT} to 0 V for a minimum of 10 μ s before powering the V_{CCINT} and V_{CCIO} up again. Once V_{CCINT} rises from 0 V back to approximately 1.55 V, the SRAM download restarts and the device begins to operate after t_{CONFIG} time has passed.

Figure 4–5 shows the voltages for POR of MAX II, MAX IIG, and MAX IIZ devices during power-up into user mode and from user mode to power-down or brown-out.



All V_{CCINT} and V_{CCIO} pins of all banks must be powered on MAX II devices before entering user mode.

Referenced Documents

This chapter references the following documents:

- *DC and Switching Characteristics* chapter in the *MAX II Device Handbook*
- *Using MAX II Devices in Multi-Voltage Systems* chapter in the *MAX II Device Handbook*

Document Revision History

Table 4–1 shows the revision history for this chapter.

Table 4–1. Document Revision History

Date and Revision	Changes Made	Summary of Changes
October 2008, version 2.1	<ul style="list-style-type: none"> ■ Updated “MAX II Hot-Socketing Specifications” and “Power-On Reset Circuitry” sections. ■ Updated New Document Format. 	—
December 2007, version 2.0	<ul style="list-style-type: none"> ■ Updated “Hot Socketing Feature Implementation in MAX II Devices” section. ■ Updated “Power-On Reset Circuitry” section. ■ Updated Figure 4–5. ■ Added “Referenced Documents” section. 	Updated document with MAX IIZ information.
December 2006, version 1.5	<ul style="list-style-type: none"> ■ Added document revision history. 	—
February 2006, version 1.4	<ul style="list-style-type: none"> ■ Updated “MAX II Hot-Socketing Specifications” section. ■ Updated “AC and DC Specifications” section. ■ Updated “Power-On Reset Circuitry” section. 	—
June 2005, version 1.3	<ul style="list-style-type: none"> ■ Updated AC and DC specifications on page 4-2. 	—
December 2004, version 1.2	<ul style="list-style-type: none"> ■ Added content to Power-Up Characteristics section. ■ Updated Figure 4-5. 	—
June 2004, version 1.1	<ul style="list-style-type: none"> ■ Corrected Figure 4-2. 	—

Recommended Operating Conditions

Table 5–2 shows the MAX II device family recommended operating conditions.

Table 5–2. MAX II Device Recommended Operating Conditions

Symbol	Parameter	Conditions	Minimum	Maximum	Unit
V_{CCINT} (1)	3.3-V supply voltage for internal logic and ISP	MAX II devices	3.00	3.60	V
	2.5-V supply voltage for internal logic and ISP	MAX II devices	2.375	2.625	V
	1.8-V supply voltage for internal logic and ISP	MAX IIG and MAX IIZ devices	1.71	1.89	V
V_{CCIO} (1)	Supply voltage for I/O buffers, 3.3-V operation	—	3.00	3.60	V
	Supply voltage for I/O buffers, 2.5-V operation	—	2.375	2.625	V
	Supply voltage for I/O buffers, 1.8-V operation	—	1.71	1.89	V
	Supply voltage for I/O buffers, 1.5-V operation	—	1.425	1.575	V
V_I	Input voltage	(2), (3), (4)	–0.5	4.0	V
V_O	Output voltage	—	0	V_{CCIO}	V
T_J	Operating junction temperature	Commercial range	0	85	°C
		Industrial range	–40	100	°C
		Extended range (5)	–40	125	°C

Notes to Table 5–2:

- (1) MAX II device in-system programming and/or user flash memory (UFM) programming via JTAG or logic array is not guaranteed outside the recommended operating conditions (for example, if brown-out occurs in the system during a potential write/program sequence to the UFM, users are recommended to read back UFM contents and verify against the intended write data).
- (2) Minimum DC input is –0.5 V. During transitions, the inputs may undershoot to –2.0 V for input currents less than 100 mA and periods shorter than 20 ns.
- (3) During transitions, the inputs may overshoot to the voltages shown in the following table based upon input duty cycle. The DC case is equivalent to 100% duty cycle. For more information about 5.0-V tolerance, refer to the *Using MAX II Devices in Multi-Voltage Systems* chapter in the *MAX II Device Handbook*.

V_{IN}	Max. Duty Cycle
4.0 V	100% (DC)
4.1	90%
4.2	50%
4.3	30%
4.4	17%
4.5	10%
- (4) All pins, including clock, I/O, and JTAG pins, may be driven before V_{CCINT} and V_{CCIO} are powered.
- (5) For the extended temperature range of 100 to 125° C, MAX II UFM programming (erase/write) is only supported via the JTAG interface. UFM programming via the logic array interface is not guaranteed in this range.

Table 5-6. 3.3-V LVCMOS Specifications (Part 2 of 2)

Symbol	Parameter	Conditions	Minimum	Maximum	Unit
V_{OH}	High-level output voltage	$V_{CCIO} = 3.0$, $IOH = -0.1 \text{ mA}$ (1)	$V_{CCIO} - 0.2$	—	V
V_{OL}	Low-level output voltage	$V_{CCIO} = 3.0$, $IOL = 0.1 \text{ mA}$ (1)	—	0.2	V

Table 5-7. 2.5-V I/O Specifications

Symbol	Parameter	Conditions	Minimum	Maximum	Unit
V_{CCIO}	I/O supply voltage	—	2.375	2.625	V
V_{IH}	High-level input voltage	—	1.7	4.0	V
V_{IL}	Low-level input voltage	—	-0.5	0.7	V
V_{OH}	High-level output voltage	$IOH = -0.1 \text{ mA}$ (1)	2.1	—	V
		$IOH = -1 \text{ mA}$ (1)	2.0	—	V
		$IOH = -2 \text{ mA}$ (1)	1.7	—	V
V_{OL}	Low-level output voltage	$IOL = 0.1 \text{ mA}$ (1)	—	0.2	V
		$IOL = 1 \text{ mA}$ (1)	—	0.4	V
		$IOL = 2 \text{ mA}$ (1)	—	0.7	V

Table 5-8. 1.8-V I/O Specifications

Symbol	Parameter	Conditions	Minimum	Maximum	Unit
V_{CCIO}	I/O supply voltage	—	1.71	1.89	V
V_{IH}	High-level input voltage	—	$0.65 \times V_{CCIO}$	2.25 (2)	V
V_{IL}	Low-level input voltage	—	-0.3	$0.35 \times V_{CCIO}$	V
V_{OH}	High-level output voltage	$IOH = -2 \text{ mA}$ (1)	$V_{CCIO} - 0.45$	—	V
V_{OL}	Low-level output voltage	$IOL = 2 \text{ mA}$ (1)	—	0.45	V

Table 5-9. 1.5-V I/O Specifications

Symbol	Parameter	Conditions	Minimum	Maximum	Unit
V_{CCIO}	I/O supply voltage	—	1.425	1.575	V
V_{IH}	High-level input voltage	—	$0.65 \times V_{CCIO}$	$V_{CCIO} + 0.3$ (2)	V
V_{IL}	Low-level input voltage	—	-0.3	$0.35 \times V_{CCIO}$	V
V_{OH}	High-level output voltage	$IOH = -2 \text{ mA}$ (1)	$0.75 \times V_{CCIO}$	—	V
V_{OL}	Low-level output voltage	$IOL = 2 \text{ mA}$ (1)	—	$0.25 \times V_{CCIO}$	V

Notes to Table 5-5 through Table 5-9:

- (1) This specification is supported across all the programmable drive strength settings available for this I/O standard, as shown in the *MAX II Architecture* chapter (*I/O Structure* section) in the *MAX II Device Handbook*.
- (2) This maximum V_{IH} reflects the JEDEC specification. The MAX II input buffer can tolerate a V_{IH} maximum of 4.0, as specified by the V_I parameter in Table 5-2.

Power-Up Timing

Table 5–12 shows the power-up timing characteristics for MAX II devices.

Table 5–12. MAX II Power-Up Timing

Symbol	Parameter	Device	Min	Typ	Max	Unit
$t_{\text{CONFIG}} (1)$	The amount of time from when minimum V_{CCINT} is reached until the device enters user mode (2)	EPM240	—	—	200	μs
		EPM570	—	—	300	μs
		EPM1270	—	—	300	μs
		EPM2210	—	—	450	μs

Notes to Table 5–12:

- (1) Table 5–12 values apply to commercial and industrial range devices. For extended temperature range devices, the t_{CONFIG} maximum values are as follows:

Device	Maximum
EPM240	300 μs
EPM570	400 μs
EPM1270	400 μs
EPM2210	500 μs

- (2) For more information about POR trigger voltage, refer to the *Hot Socketing and Power-On Reset in MAX II Devices* chapter in the *MAX II Device Handbook*.

Power Consumption

Designers can use the Altera® PowerPlay Early Power Estimator and PowerPlay Power Analyzer to estimate the device power.



For more information about these power analysis tools, refer to the *Understanding and Evaluating Power in MAX II Devices* chapter in the *MAX II Device Handbook* and the *PowerPlay Power Analysis* chapter in volume 3 of the *Quartus II Handbook*.

Timing Model and Specifications

MAX II devices timing can be analyzed with the Altera Quartus® II software, a variety of popular industry-standard EDA simulators and timing analyzers, or with the timing model shown in Figure 5–2.

MAX II devices have predictable internal delays that enable the designer to determine the worst-case timing of any design. The software provides timing simulation, point-to-point delay prediction, and detailed timing analysis for device-wide performance evaluation.

Table 5-13. MAX II Device Timing Model Status (Part 2 of 2)

Device	Preliminary	Final
EPM1270	—	✓
EPM2210	—	✓

Note to Table 5-13:

- (1) The MAX IIZ device timing models are only available in the Quartus II software version 8.0 and later.

Performance

Table 5-14 shows the MAX II device performance for some common designs. All performance values were obtained with the Quartus II software compilation of megafunctions. Performance values for -3, -4, and -5 speed grades are based on an EPM1270 device target, while -6, -7, and -8 speed grades are based on an EPM570Z device target.

Table 5-14. MAX II Device Performance

Resource Used	Design Size and Function	Resources Used			Performance						Unit
					MAX II / MAX IIG			MAX IIZ			
		Mode	LEs	UFM Blocks	−3 Speed Grade	−4 Speed Grade	−5 Speed Grade	−6 Speed Grade	−7 Speed Grade	−8 Speed Grade	
LE	16-bit counter (1)	—	16	0	304.0	247.5	201.1	184.1	123.5	118.3	MHz
	64-bit counter (1)	—	64	0	201.5	154.8	125.8	83.2	83.2	80.5	MHz
	16-to-1 multiplexer	—	11	0	6.0	8.0	9.3	17.4	17.3	20.4	ns
	32-to-1 multiplexer	—	24	0	7.1	9.0	11.4	12.5	22.8	25.3	ns
	16-bit XOR function	—	5	0	5.1	6.6	8.2	9.0	15.0	16.1	ns
	16-bit decoder with single address line	—	5	0	5.2	6.6	8.2	9.2	15.0	16.1	ns
UFM	512 × 16	None	3	1	10.0	10.0	10.0	10.0	10.0	10.0	MHz
	512 × 16	SPI (2)	37	1	8.0	8.0	8.0	9.7	9.7	9.7	MHz
	512 × 8	Parallel (3)	73	1	(4)	(4)	(4)	(4)	(4)	(4)	MHz
	512 × 16	I ² C (3)	142	1	100 (5)	100 (5)	100 (5)	100 (5)	100 (5)	100 (5)	kHz

Notes to Table 5-14:

- (1) This design is a binary loadable up counter.
- (2) This design is configured for read-only operation in Extended mode. Read and write ability increases the number of LEs used.
- (3) This design is configured for read-only operation. Read and write ability increases the number of LEs used.
- (4) This design is asynchronous.
- (5) The I²C megafunction is verified in hardware up to 100-kHz serial clock line (SCL) rate.

Internal Timing Parameters

Internal timing parameters are specified on a speed grade basis independent of device density. Table 5-15 through Table 5-22 describe the MAX II device internal timing microparameters for logic elements (LEs), input/output elements (IOEs), UFM blocks, and MultiTrack interconnects. The timing values for -3, -4, and -5 speed grades shown in Table 5-15 through Table 5-22 are based on an EPM1270 device target, while -6, -7, and -8 speed grade values are based on an EPM570Z device target.



For more explanations and descriptions about each internal timing microparameters symbol, refer to the *Understanding Timing in MAX II Devices* chapter in the *MAX II Device Handbook*.

Table 5-15. LE Internal Timing Microparameters

Symbol	Parameter	MAX II / MAX IIG						MAX IIZ						Unit
		-3 Speed Grade		-4 Speed Grade		-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
t _{LUT}	LE combinational LUT delay	—	571	—	742	—	914	—	1,215	—	2,247	—	2,247	ps
t _{COMB}	Combinational path delay	—	147	—	192	—	236	—	243	—	305	—	309	ps
t _{CLR}	LE register clear delay	238	—	309	—	381	—	401	—	541	—	545	—	ps
t _{PRE}	LE register preset delay	238	—	309	—	381	—	401	—	541	—	545	—	ps
t _{SU}	LE register setup time before clock	208	—	271	—	333	—	260	—	319	—	321	—	ps
t _H	LE register hold time after clock	0	—	0	—	0	—	0	—	0	—	0	—	ps
t _{CO}	LE register clock-to-output delay	—	235	—	305	—	376	—	380	—	489	—	494	ps
t _{CLKHL}	Minimum clock high or low time	166	—	216	—	266	—	253	—	335	—	339	—	ps
t _C	Register control delay	—	857	—	1,114	—	1,372	—	1,356	—	1,722	—	1,741	ps

Table 5-20. t_{XZ} IOE Microparameter Adders for Slow Slew Rate

Standard		MAX II / MAX IIG						MAX IIZ						Unit
		-3 Speed Grade		-4 Speed Grade		-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
3.3-V LV TTL	16 mA	—	206	—	–20	—	–247	—	1,433	—	1,446	—	1,454	ps
	8 mA	—	891	—	665	—	438	—	1,332	—	1,345	—	1,348	ps
3.3-V LV CMOS	8 mA	—	206	—	–20	—	–247	—	1,433	—	1,446	—	1,454	ps
	4 mA	—	891	—	665	—	438	—	1,332	—	1,345	—	1,348	ps
2.5-V LV TTL / LV CMOS	14 mA	—	222	—	–4	—	–231	—	213	—	208	—	213	ps
	7 mA	—	943	—	717	—	490	—	166	—	161	—	166	ps
3.3-V PCI	20 mA	—	161	—	210	—	258	—	1,332	—	1,345	—	1,348	ps

 The default slew rate setting for MAX II devices in the Quartus II design software is “fast”.

Table 5-21. UFM Block Internal Timing Microparameters (Part 1 of 3)

Symbol	Parameter	MAX II / MAX IIG						MAX IIZ						Unit
		-3 Speed Grade		-4 Speed Grade		-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
t _{ACLK}	Address register clock period	100	—	100	—	100	—	100	—	100	—	100	—	ns
t _{ASU}	Address register shift signal setup to address register clock	20	—	20	—	20	—	20	—	20	—	20	—	ns
t _{AH}	Address register shift signal hold to address register clock	20	—	20	—	20	—	20	—	20	—	20	—	ns
t _{ADS}	Address register data in setup to address register clock	20	—	20	—	20	—	20	—	20	—	20	—	ns
t _{ADH}	Address register data in hold from address register clock	20	—	20	—	20	—	20	—	20	—	20	—	ns
t _{DCLK}	Data register clock period	100	—	100	—	100	—	100	—	100	—	100	—	ns
t _{DSS}	Data register shift signal setup to data register clock	60	—	60	—	60	—	60	—	60	—	60	—	ns
t _{DSH}	Data register shift signal hold from data register clock	20	—	20	—	20	—	20	—	20	—	20	—	ns

Table 5–26 shows the external I/O timing parameters for EPM2210 devices.

Table 5–26. EPM2210 Global Clock External I/O Timing Parameters

Symbol	Parameter	Condition	MAX II / MAX IIG						Unit
			–3 Speed Grade		–4 Speed Grade		–5 Speed Grade		
			Min	Max	Min	Max	Min	Max	
t _{PD1}	Worst case pin-to-pin delay through 1 look-up table (LUT)	10 pF	—	7.0	—	9.1	—	11.2	ns
t _{PD2}	Best case pin-to-pin delay through 1 LUT	10 pF	—	3.7	—	4.8	—	5.9	ns
t _{SU}	Global clock setup time	—	1.2	—	1.5	—	1.9	—	ns
t _H	Global clock hold time	—	0	—	0	—	0	—	ns
t _{CO}	Global clock to output delay	10 pF	2.0	4.6	2.0	6.0	2.0	7.4	ns
t _{CH}	Global clock high time	—	166	—	216	—	266	—	ps
t _{CL}	Global clock low time	—	166	—	216	—	266	—	ps
t _{CNT}	Minimum global clock period for 16-bit counter	—	3.3	—	4.0	—	5.0	—	ns
f _{CNT}	Maximum global clock frequency for 16-bit counter	—	—	304.0 (1)	—	247.5	—	201.1	MHz

Note to Table 5–26:

- (1) The maximum frequency is limited by the I/O standard on the clock input pin. The 16-bit counter critical delay performs faster than this global clock input pin maximum frequency.

External Timing I/O Delay Adders

The I/O delay timing parameters for I/O standard input and output adders, and input delays are specified by speed grade independent of device density.

Table 5–27 through Table 5–31 show the adder delays associated with I/O pins for all packages. The delay numbers for –3, –4, and –5 speed grades shown in Table 5–27 through Table 5–33 are based on an EPM1270 device target, while –6, –7, and –8 speed grade values are based on an EPM570Z device target. If an I/O standard other than 3.3-V LVTTTL is selected, add the input delay adder to the external t_{SU} timing parameters shown in Table 5–23 through Table 5–26. If an I/O standard other than 3.3-V LVTTTL with 16 mA drive strength and fast slew rate is selected, add the output delay adder to the external t_{CO} and t_{PD} shown in Table 5–23 through Table 5–26.

Table 5–27. External Timing Input Delay Adders (Part 1 of 2)

I/O Standard		MAX II / MAX IIG						MAX IIZ						Unit
		–3 Speed Grade		–4 Speed Grade		–5 Speed Grade		–6 Speed Grade		–7 Speed Grade		–8 Speed Grade		
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
3.3-V LV TTL	Without Schmitt Trigger	—	0	—	0	—	0	—	0	—	0	—	0	ps
	With Schmitt Trigger	—	334	—	434	—	535	—	387	—	434	—	442	ps